

Naoki Yokoyama

was born in Osaka, Japan, on March 28, 1949. He received the B. S. degree in physics from Osaka City University, in 1971, and the M. S. degree in physics in 1973 and the Ph. D. degree in electrical engineering in 1984, both from Osaka University. In 1973, he joined the Semiconductor Devices Laboratory of Fujitsu Laboratories Ltd., Kanagawa, Japan. His work there has focused on the research and development of compound semiconductor devices. Highlights include the development of self-aligned GaAs MESFET's using refractory-metal-silicide Schottky gates, the first success in fabricating hot-electron transistors, and the invention of resonant-tunneling transistors.

Dr. Yokoyama is currently a Fellow of Fujitsu Laboratories Ltd., and General Manager of Nanoelectronics Research Center. He is also a Fellow of Fujitsu Laboratories of Europe Limited. He received many awards including 1987 GaAs Symposium Young Scientist Award and 1998 IEEE Morris N. Liebmann Memorial Award. He was elected Fellow of IEEE in 2000, Fellow of IEICE (the Institute of Electronics, Information and Communication Engineers) in 2003, and Fellow of Applied Physics Society in 2007. He is also currently a Visiting Professor of the University of Tokyo.